

Electronic Supplementary Information

[Ge(TeⁿBu)₄] – a single source precursor for the chemical vapour deposition of germanium telluride thin films

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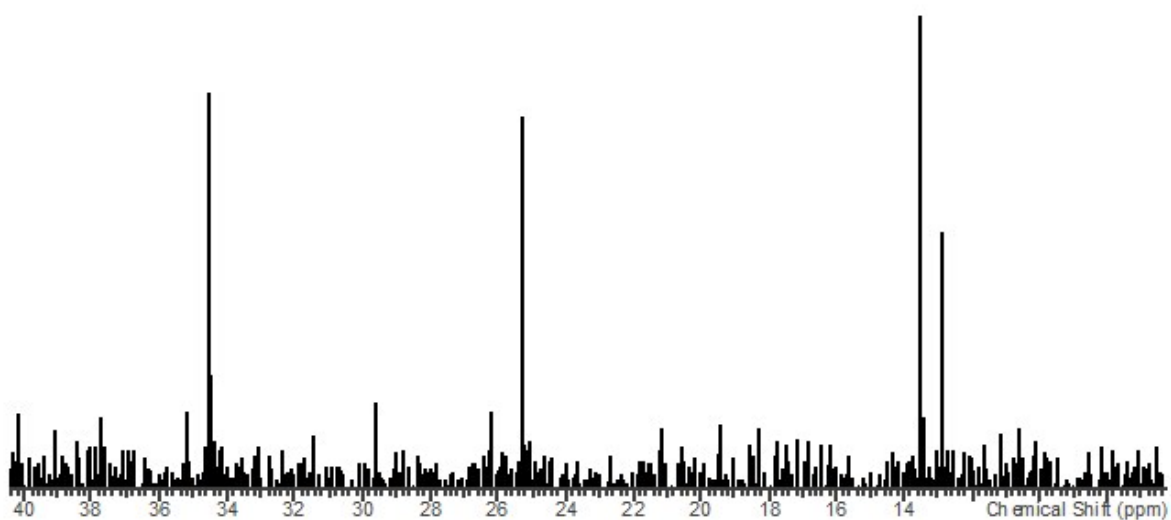


Figure S1: The ¹³C{¹H} NMR spectrum of [Ge(TeⁿBu)₄] prepared via Method 2 in CDCl₃ at 295 K.

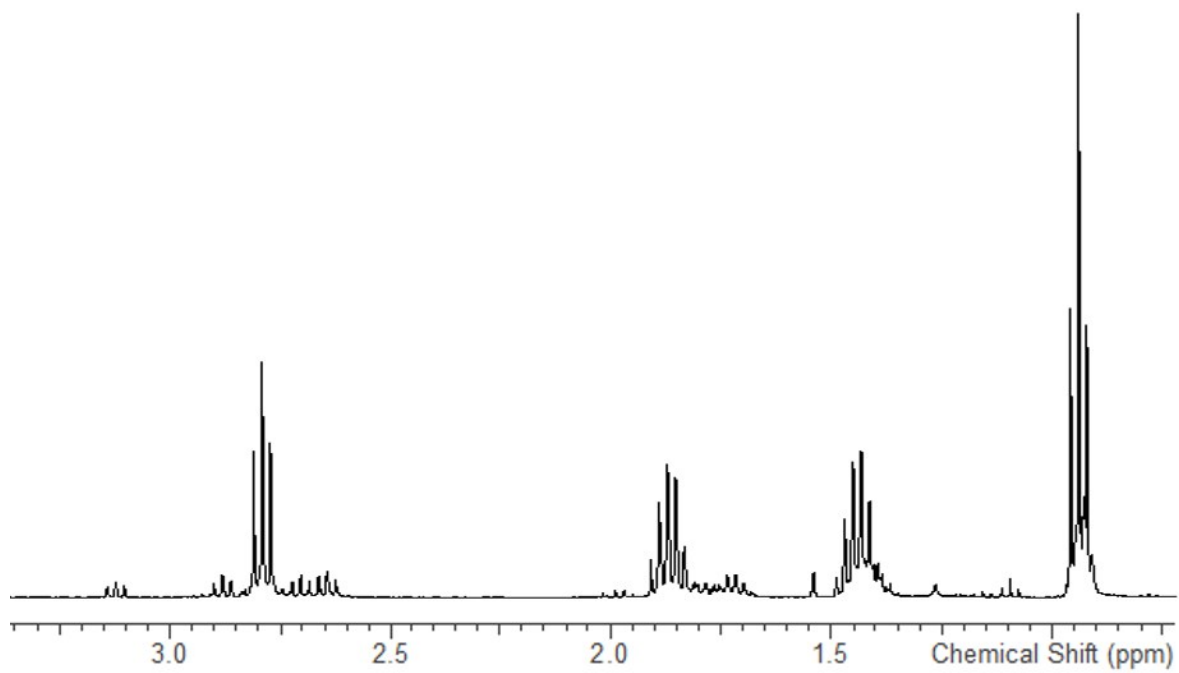


Figure S2: The ^1H NMR spectrum of $[\text{Ge}(\text{Te}^n\text{Bu})_4]$ prepared via Method 2, in CDCl_3 at 295 K.

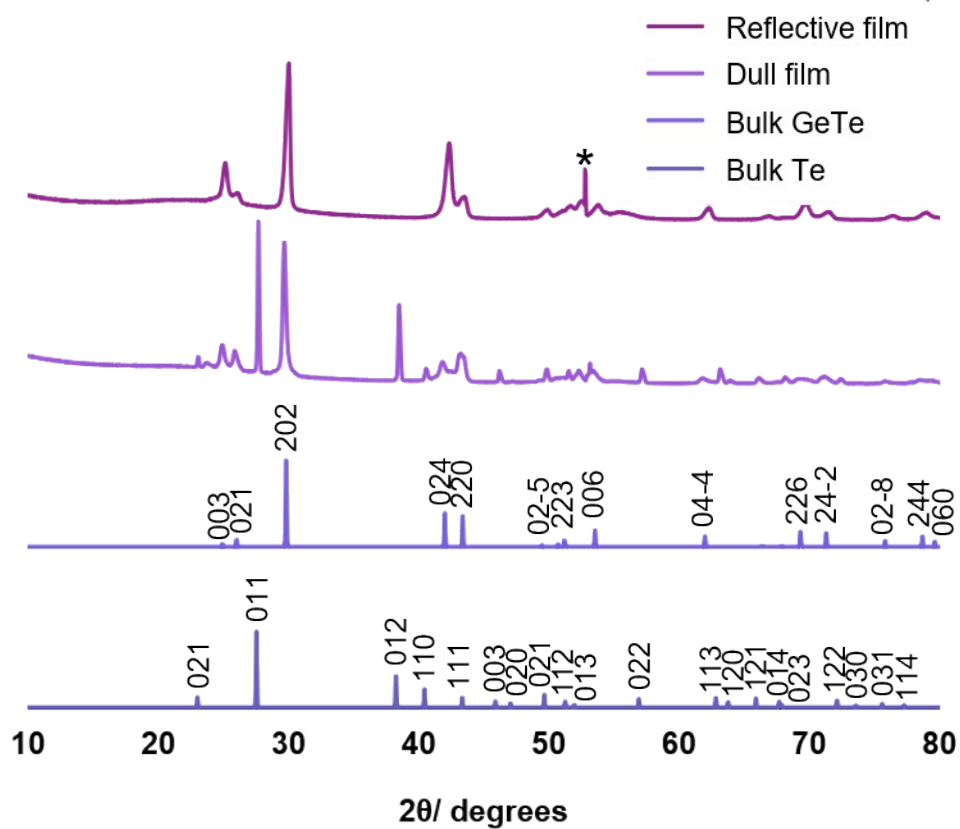


Figure S3: GIXRD pattern from two regions (reflective and dull) of a thin film deposited onto SiO₂ at 723 K /0.02 mmHg from [Ge(TeⁿBu)₄] synthesised in Method 1 and indexed XRD patterns for bulk GeTe and Te. The peak due to the Si underlying the SiO₂ in the substrate is marked *.